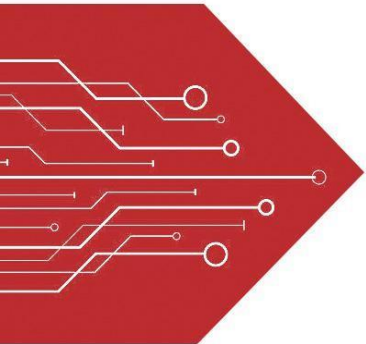


MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT

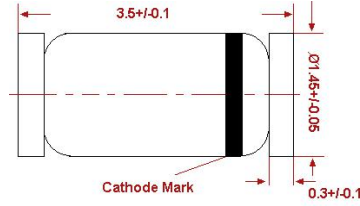


PLED

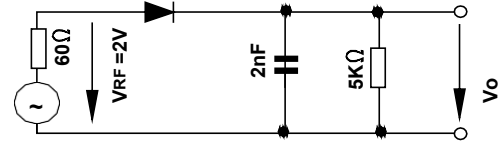
Product data sheet

Features

power dissipation
IF:200mA
VR:75V
PKG:LL34 glass case



Glass case MiniMELF
Dimensions in mm



Rectification Efficiency Measurement Circuit

LL-34

REEL SPECIFICATION

P/N	PKG	QTY
LL4148-MS	LL34	2500

Absolute Maximum Ratings (T_a = 25 °C)

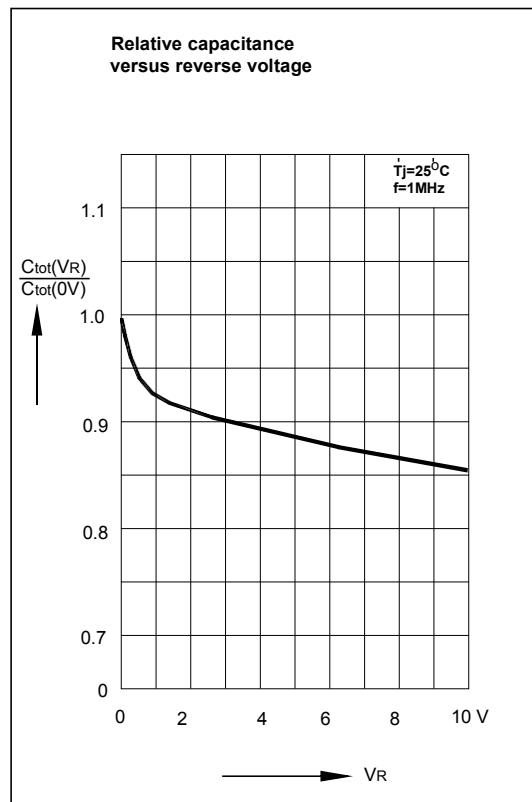
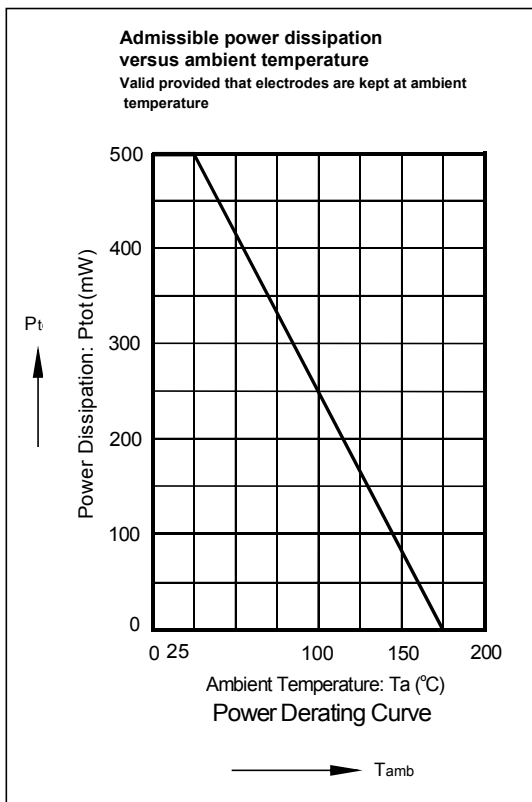
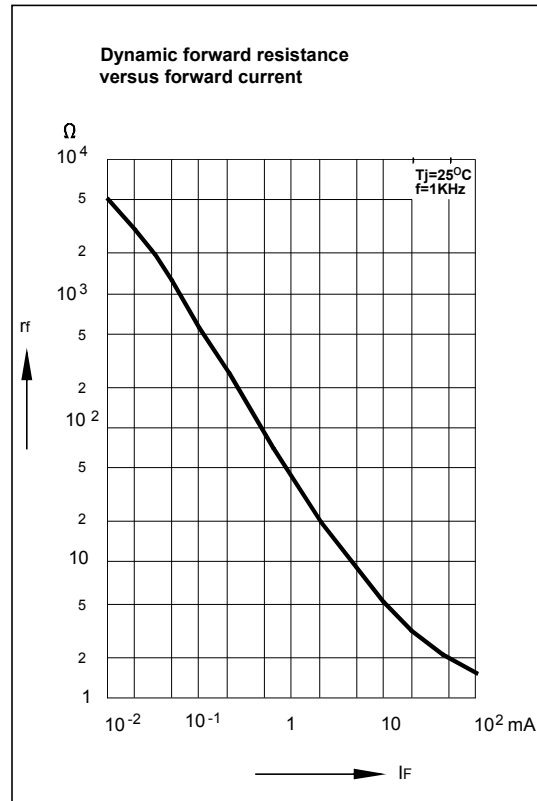
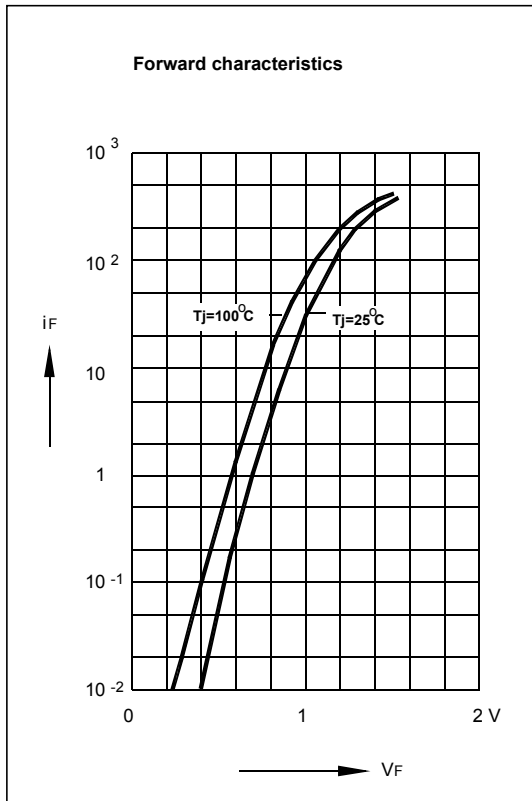
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	100	V
Reverse Voltage	V _R	75	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Non-repetitive Peak Forward Surge Current	I _{FSM}	0.5 1 4	A
		at t = 1 s	
		at t = 1 ms	
		at t = 1 μs	
Power Dissipation	P _{tot}	500 ¹⁾	mW
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _{stg}	- 65 to + 175	°C

¹⁾ Valid provided that electrodes are kept at ambient temperature.

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 10 mA	V _F	-	1	V
Leakage Current at V _R = 20 V	I _R	-	25	nA
at V _R = 75 V	I _R	-	5	μA
at V _R = 20 V, T _j = 150 °C	I _R	-	50	μA
Reverse Breakdown Voltage tested with 100 μA Pulses	V _{(BR)R}	100	-	V
Capacitance at V _R = 0, f = 1 MHz	C _{tot}	-	4	pF
Voltage Rise when Switching ON tested with 50 mA Forward Pulses tp = 0.1 s, Rise Time < 30 ns, fp = 5 to 100 KHz	V _{fr}	-	2.5	V
Reverse Recovery Time at I _F = 10 mA to I _R = 1 mA, V _R = 6 V, R _L = 100 Ω	t _{rr}	-	4	ns
Thermal Resistance Junction to Ambient Air	R _{thA}	-	0.35 ¹⁾	K/mW
Rectification Efficiency at f = 100 MHz, V _{RF} = 2 V	η _V	0.45	-	-

¹⁾ Valid provided that electrodes are kept at ambient temperature.



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